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Thermoelectric properties of nanostructured bismuth-telluride thin films grown using pulsed laser deposition

Phuoc Huu Le^a, Chien-Neng Liao^b, Chih Wei Luo^{c,†}, Jihperng Leu^{a,*}

^a Department of Materials Science and Engineering, National Chiao Tung University, Hsinchu, 30049 Taiwan, ROC

^b Department of Materials Science and Engineering, National Tsing-Hua University, Hsinchu 30013, Taiwan, ROC

^c Department of Electrophysics, National Chiao Tung University, Hsinchu, 30010 Taiwan, ROC

[†]cwluo@mail.nctu.edu.tw Tel: +886-35712121-56196

^{*}jimleu@mail.nctu.edu.tw Tel: +886-35131420

Abstract

Nanostructured n-type bismuth telluride (Bi_2Te_3) thin films were grown on SiO_2/Si (100) substrates at argon ambient pressure (P_{Ar}) of 80 Pa by pulsed laser deposition (PLD). The effects of film morphologies, structures, and compositions on the thermoelectric properties were investigated. At a substrate temperature (T_s) of 220–340 °C, stoichiometric films with highly (001)-oriented and layered structures showed the best properties, with a carrier mobility μ of 83.9 – 122.3 cm^2/Vs , an absolute Seebeck coefficient $|\alpha|$ of 172.8 – 189.7 $\mu\text{V}/\text{K}$, and a remarkably high power factor (PF) of 18.2 – 24.3 $\mu\text{Wcm}^{-1}\text{K}^{-2}$. By contrast, the Te-rich films deposited at $T_s \leq 120$ °C with (015)-preferred orientations and columnar-small grain structures or the Te-deficient film deposited at 380 °C with Bi_4Te_5 polyhedron structure possessed poor properties, with $\mu < 10.0$ cm^2/Vs , $|\alpha| < 54$ $\mu\text{V}/\text{K}$, and PFs ≤ 0.44 $\mu\text{Wcm}^{-1}\text{K}^{-2}$. The morphology of highly (001) oriented-layered structures and the stoichiometry predominantly contribute to the substantial enhancement of μ and $|\alpha|$, respectively, resulting in remarkable enhancement in PF.

Key words: Bi_2Te_3 , thermoelectric properties, nanostructures, pulsed laser deposition (PLD).

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